

Rafik M Imamov

List of Publications by Year in descending order

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Version: 2024-02-01

13
papers

110
citations

1684188

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h-index

1372567

10
g-index

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13
docs citations

13
times ranked

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citing authors

#	ARTICLE	IF	CITATIONS
1	Structural and electrical properties of InAlAs/InGaAs/InAlAs HEMT heterostructures on InP substrates with InAs inserts in quantum well. <i>Crystallography Reports</i> , 2014, 59, 900-907.	0.6	3
2	X-Ray diffractometry of metamorphic nanoheterostructures. <i>Crystallography Reports</i> , 2014, 59, 258-265.	0.6	8
3	Electrophysical characteristics and structural parameters of metamorphic HEMT nanoheterostructures In _{0.7} Al _{0.3} As/In _{0.7} Ga _{0.3} As/In _{0.7} Al _{0.3} As containing superlattices with different numbers of periods in the metamorphic buffer. <i>Crystallography Reports</i> , 2014, 59, 425-429.	0.6	2
4	Metamorphic InAlAs/InGaAs/InAlAs/GaAs HEMT heterostructures containing strained superlattices and inverse steps in the metamorphic buffer. <i>Journal of Crystal Growth</i> , 2013, 366, 55-60.	1.5	23
5	Study of new designs for the InAlAs metamorphic buffer on GaAs substrates with distributed compensation of elastic deformations. <i>Semiconductors</i> , 2013, 47, 997-1002.	0.5	8
6	Study of the influence of strained superlattices introduced into a metamorphic buffer on the electrophysical properties and the atomic structure of InAlAs/InGaAs MHEMT heterostructures. <i>Semiconductors</i> , 2013, 47, 532-537.	0.5	4
7	Electrical and structural characteristics of metamorphic In _{0.38} Al _{0.62} As/In _{0.37} Ga _{0.63} As/In _{0.38} Al _{0.62} As HEMT nanoheterostructures. <i>Crystallography Reports</i> , 2013, 58, 914-919.	0.6	2
8	Structural and electrical properties of quantum wells with nanoscale InAs inserts in In _y Al _{1-y} As/In _x Ga _{1-x} As heterostructures on InP substrates. <i>Crystallography Reports</i> , 2011, 56, 298-309.	0.6	11
9	The electrical and structural properties of In _y Ga _{1-y} As/In _x Al _{1-x} As/InP quantum wells with different InAs content. <i>Crystallography Reports</i> , 2010, 55, 6-9.	0.6	0
10	Study of the relationship between the crystal structure of nanolayers and electrical properties in Al _x Ga _{1-x} As/In _y Ga _{1-y} As pseudobinary heterostructures by double-crystal X-ray diffraction. <i>Crystallography Reports</i> , 2008, 53, 183-186.	0.6	0
11	Structural characterization of interfaces in the Al _x Ga _{1-x} As/GaAs/Al _x Ga _{1-x} As heterostructures by high-resolution X-ray reflectometry and diffractometry. <i>Crystallography Reports</i> , 2005, 50, 739-750.	0.6	2
12	<title>Structural diagnostics of quantum layers by x-ray diffraction and standing waves</title>. , 2004, 5401, 543.		5
13	Asymmetric X-Ray Diffraction. <i>Crystallography Reviews</i> , 1992, 3, 157-226.	1.5	42